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DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

Check for Samples: SN74LVC2G126-EP

FEATURES

- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 6.8 ns at 3.3 V
- Low Power Consumption, 10-µA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce)
 <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

SUPPORTS DEFENSE, AEROSPACE, AND MEDICAL APPLICATIONS

- Controlled Baseline
- · One Assembly and Test Site
- One Fabrication Site
- Available in Military (–55°C to 125°C)
 Temperature Range
- · Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability

DCU PACKAGE (TOP VIEW)

20E
] 1Y
2A

DESCRIPTION

This dual bus buffer gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G126 is a dual bus driver/line driver with 3-state outputs. The outputs are disabled when the associated output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

ORDERING INFORMATION(1)

TJ	PACKA	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER
-55°C to 125°C	TAORAGE		CLVC2G126MDCUTEP	CEPR	V62/14604-01XE

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (2) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

Function Table (Each Buffer)

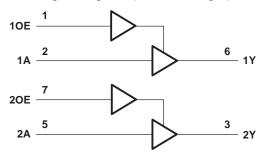
INP	UTS	OUTPUT
OE	Α	Υ
Н	Н	Н
Н	L	L
L	X	Z



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Logic Diagram (Positive Logic)



ABSOLUTE MAXIMUM RATINGs(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range (2)	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high-	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	V _I < 0		-50	mA
I_{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T_{J}	Absolute maximum junction temperature range	-55	150	ô	
T _{stg}	Storage temperature range		-65	150	ô

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

THERMAL INFORMATION

		SN74LVC2G126-EP	
	THERMAL METRIC ⁽¹⁾	DCU	UNITS
		8 PINS	
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	204.3	
θ_{JCtop}	Junction-to-case (top) thermal resistance (3)	78	
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	83	00.004
ΨЈТ	Junction-to-top characterization parameter ⁽⁵⁾	7.6	°C/W
ΨЈВ	Junction-to-board characterization parameter ⁽⁶⁾	82.6	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	N/A	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

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⁽³⁾ The value of V_{CC} is provided in the recommended operating conditions table.



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RECOMMENDED OPERATING CONDITIONS(1)

			MIN	MAX	UNIT
V	Cupply valtage	Operating	1.65	5.5	V
V_{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
V	High lavel innut values	V _{CC} = 2.3 V to 2.7 V	1.7		V
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	
V	Lauria de la contra del la contra del la contra del la contra de la contra del la contra de la contra de la contra del la co	V _{CC} = 2.3 V to 2.7 V		0.7	V
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
VI	Input voltage		0	5.5	V
V	Outrot valle ve	High or low state	0	V_{CC}	V
V _O	O Output voltage	3-state	0	5.5	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
I _{OH}	High-level output current	V _{CC} = 3 V		-16	mA
		v _{CC} = 3 v		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V _{CC} = 3 V		16	mA
		v _{CC} = 3 v		24	
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$	5		
TJ	Operating virtual junction temperature		-55	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Product Folder Links: SN74LVC2G126-EP

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ELECTRICAL CHARACTERISTICS

These specifications apply for $-55^{\circ}\text{C} \le \text{T}_{\text{J}} \le 125^{\circ}\text{C}$ (unless otherwise noted)

F	PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾	MAX	UNIT
		$I_{OH} = -100 \ \mu A$	1.65 V to 5.5 V	$V_{CC} - 0.1$			
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2			
V _{OH}		$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			V
VOH		$I_{OH} = -16 \text{ mA}$	3 V	2.4			V
		$I_{OH} = -24 \text{ mA}$	3 V	2.3			
		$I_{OH} = -32 \text{ mA}$	4.5 V	3.8			
		I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	
		I _{OL} = 4 mA	1.65 V			0.45	
.,		I _{OL} = 8 mA	2.3 V			0.3	V
V _{OL}		I _{OL} = 16 mA	3 V			0.4	v
		I _{OL} = 24 mA	3 V			0.55	
		I _{OL} = 32 mA	4.5 V			0.55	
I	A or OE inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5	μΑ
I _{off}		V_1 or $V_0 = 5.5 \text{ V}$	0			±10	μA
I_{OZ}		$V_O = 0$ to 5.5 V	3.6 V			10	μA
I _{CC}		$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V			10	μA
ΔI_{CC}		One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or	r GND 3 V to 5.5 V			500	μA
	Data inputs			3.5			
Cı	Control inputs	$V_{I} = V_{CC}$ or GND	3.3 V		4		pF
Co		$V_O = V_{CC}$ or GND	3.3 V		6.5		pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_J = 25°C.

SWITCHING CHARACTERISTICS

These specifications apply for $-55^{\circ}\text{C} \le T_{J} \le 125^{\circ}\text{C}$ (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5		UNIT
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	3.5	15.2	1.7	8.6	1.4	6.8	1	5.5	ns
t _{en}	OE	Υ	3.5	15.2	1.7	8.6	1.5	6.8	1	5.5	ns
t _{dis}	OE	Υ	1.7	12.6	1	5.7	1	4.5	0.1	3.3	ns

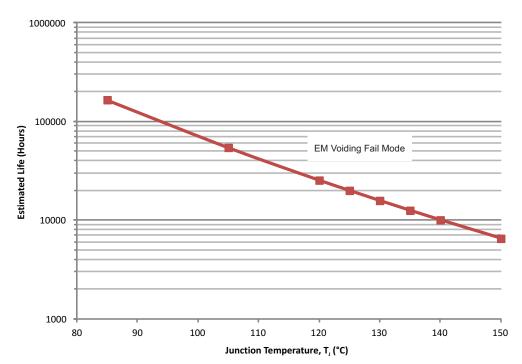
OPERATING CHARACTERISTICS

 $T_J = 25^{\circ}$

	PARAMETER	?	TEST CONDITIONS	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	V _{CC} = 5 V TYP	UNIT
0	Power dissipation	Outputs enabled	f 10 MH-	19	19	20	22	F
C _{pd} capacitance		Outputs disabled	f = 10 MHz	2	2	2	3	pF

Product Folder Links: SN74LVC2G126-EP

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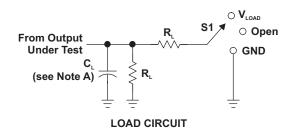
- (1) See datasheet for absolute maximum and minimum recommended operating conditions.
- (2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- (3) Enhanced plastic product disclaimer applies.

Figure 1. SN74LVC2G126-EP Operating Life Derating Chart

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PARAMETER MEASUREMENT INFORMATION



 $5 V \pm 0.5 V$

 V_{cc}

≤2.5 ns

TEST	S1
t _{PLH} /t _{PHL}	Open
$t_{_{\mathrm{PLZ}}}/t_{_{\mathrm{PZL}}}$	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

.,	INI	PUTS		.,		_		
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _A	
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V	
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V	
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V	

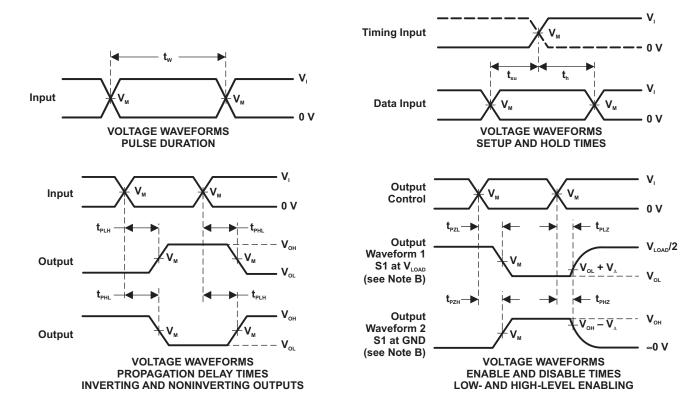
 $V_{cc}/2$

2 × V_{cc}

50 pF

500 Ω

0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_o = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $\dot{t}_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}$.
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

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PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CLVC2G126MDCUTEP	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CEPR	Samples
V62/14604-01XE	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CEPR	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

OTHER QUALIFIED VERSIONS OF SN74LVC2G126-EP:

● Catalog: SN74LVC2G126

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NOTE: Qualified Version Definitions:

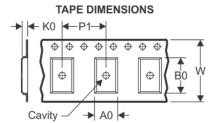
• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 3-Aug-2017

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CLVC2G126MDCUTEP	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3

www.ti.com 3-Aug-2017

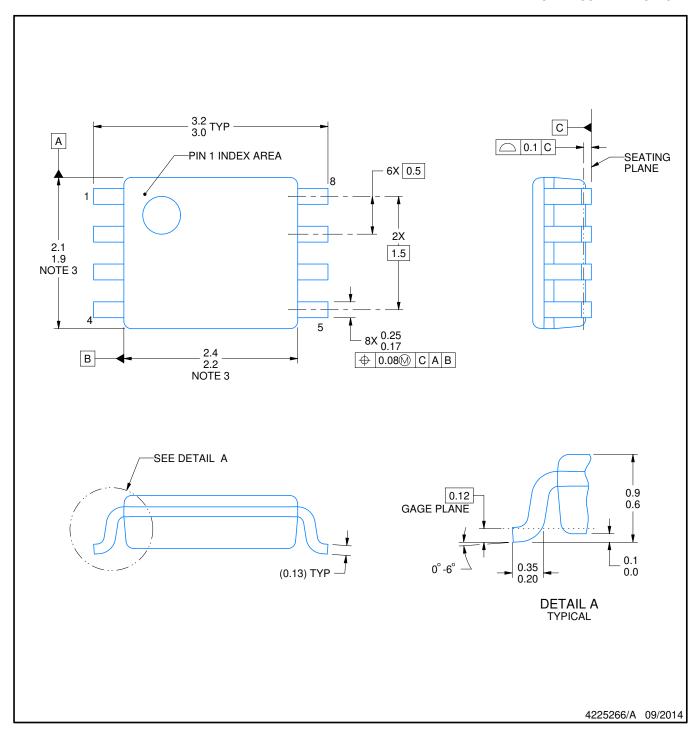


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CLVC2G126MDCUTEP	VSSOP	DCU	8	250	202.0	201.0	28.0	



SMALL OUTLINE PACKAGE



NOTES:

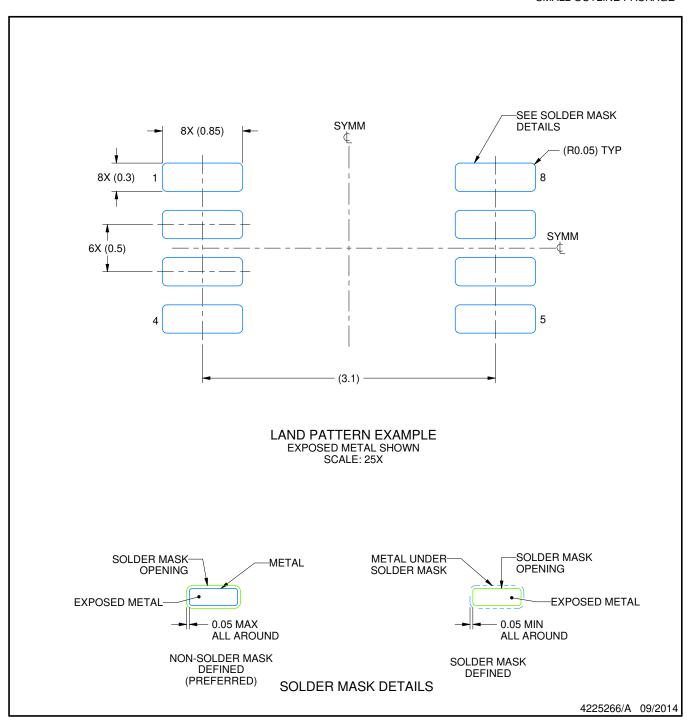
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-187 variation CA.



SMALL OUTLINE PACKAGE



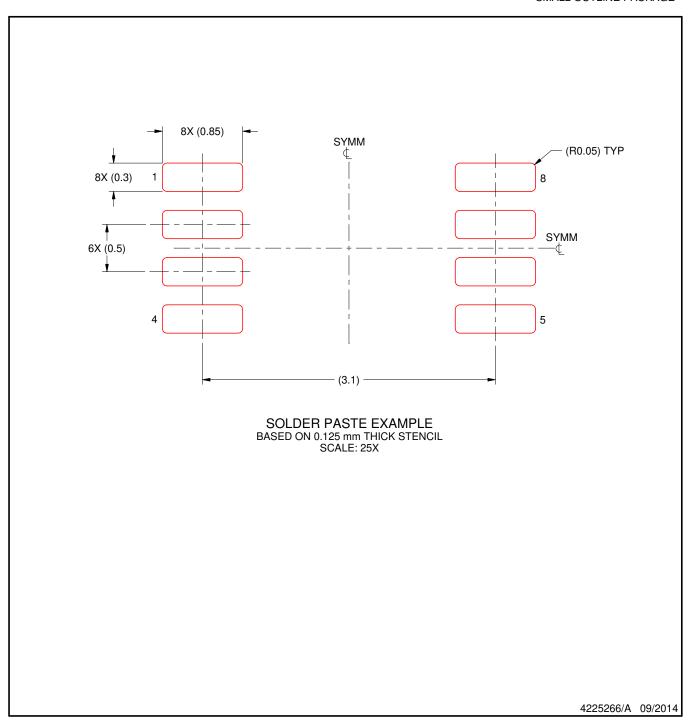
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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